



60V PNP LOW VCE(SAT) TRANSISTOR IN SOT223

Description

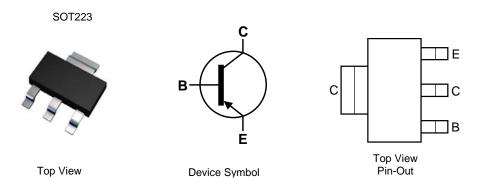
This bipolar junction transistor (BJT) is designed to meet the stringent requirements of automotive applications.

Features

- Ideally Suited for Automated Assembly Processes
- Ultra Low Collector-Emitter Saturation Voltage
- Complementary NPN Type Available (DSS60601MZ4Q)
- Ideal for Medium Power Switching or Amplification Applications
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

Mechanical Data

- Case: SOT223
- Case Material: Molded Plastic. "Green" Molding Compound.
- UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 (§3)
- Weight: 0.112 grams (Approximate)



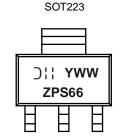
Ordering Information (Notes 4 and 5)

Product	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
DSS60600MZ4Q-13	Automotive	ZPS66	13	12	2500

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to https://www.diodes.com/quality/.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



ZPS66 = Product Type Marking Code YWW = Date Code Marking Y = Last Digit of Year (ex: 8 = 2018) WW = Week Code 01 - 52



Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-100	V
Collector-Emitter Voltage	V _{CEO}	-60	V
Emitter-Base Voltage	V _{EBO}	-7	V
Continuous Collector Current	Ic	-6	Α
Peak Pulse Current	I _{CM}	-12	Α

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Power Dissipation	(Note 6)	0	1.2	W
Fower Dissipation	(Note 7)	PD	2.0	W
Thermal Resistance, Junction to Ambient	(Note 6)	0	104	°C/W
mermai Resistance, Junction to Ambient	(Note 7)	$R_{\Theta JA}$	62.5	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C	

ESD Ratings (Note 8)

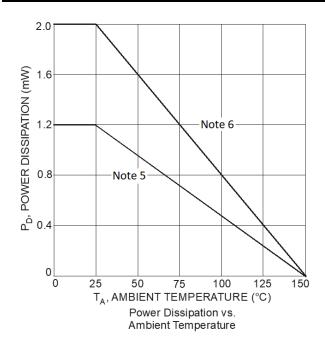
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge—Human Body Model	ESD HBM	4000	V	3A
Electrostatic Discharge—Machine Model	ESD MM	400	V	С

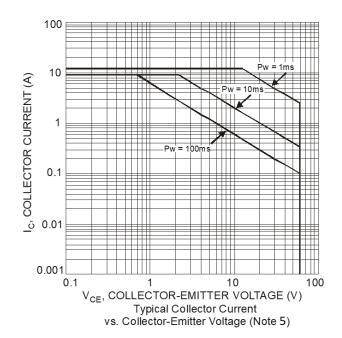
Notes:

- 6. Device mounted on FR-4 PCB with minimum recommended pad layout.
- 7. Device mounted on Polymide PCB with 330mm² 2oz. Copper pad layout. 8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



Thermal Characteristics and Derating Information







Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

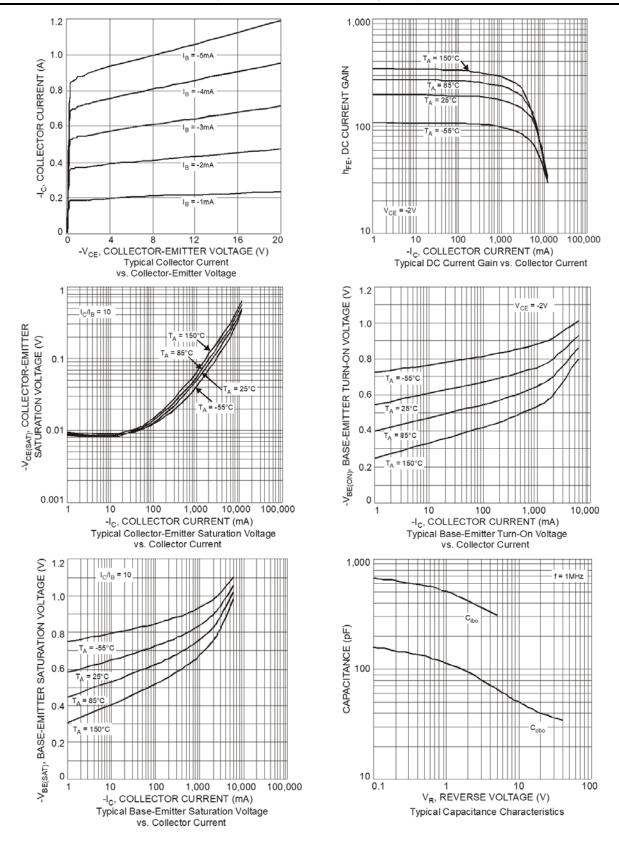
Characteristic	Symbol	Min	Тур	Max	Unit	Test Conditions
OFF CHARACTERISTICS						
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-100		1	V	$I_{C} = -100 \mu A$
Collector-Emitter Breakdown Voltage (Note 9)	$V_{(BR)CEO}$	-60			V	I _C = -10mA
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-7		_	V	$I_E = -100 \mu A$
Collector-Base Cutoff Current	I _{CBO}	_	_	-100	nA	$V_{CB} = -100V, I_{E} = 0$
Collector-base Cuton Current		_	_	-50	μΑ	$V_{CB} = -100V, I_{E} = 0, T_{A} = 150^{\circ}C$
Emitter-Base Cutoff Current	I _{EBO}		_	-100	nA	$V_{EB} = -6V, I_C = 0$
ON CHARACTERISTICS (Note 9)						
		150	_	_		$V_{CE} = -2V, I_{C} = -0.5A$
DC Current Gain	h _{FE}	120	_	360	_	$V_{CE} = -2V, I_{C} = -1A$
Do Guirent Gain	IIFE	100	_	_		$V_{CE} = -2V, I_{C} = -2A$
		70		1		$V_{CE} = -2V, I_{C} = -6A$
		_		-50		$I_C = -0.1A$, $I_B = -2mA$
		_	-50	-70		$I_C = -1A$, $I_B = -100mA$
Collector-Emitter Saturation Voltage	V _{CE} (SAT)	_	-90	-120		$I_C = -2A$, $I_B = -200mA$
		_		-250		$I_C = -3A$, $I_B = -60mA$
		_	_	-350		$I_C = -6A, I_B = -600mA$
Equivalent On-Resistance	R _{CE(SAT)}	_	45	60	mΩ	$I_C = -2A$, $I_B = -200mA$
Base-Emitter Saturation Voltage	V _{BE(SAT)}	_	_	-1.0	V	$I_C = 1A$, $I_B = -100mA$
Base-Emitter Turn-on Voltage	V _{BE(ON)}	_		-0.9	V	$V_{CE} = -2V, I_{C} = -1A$
SMALL SIGNAL CHARACTERISTICS						
Transition Frequency	f _T	100			MHz	$V_{CE} = -10V, I_{C} = -100mA,$ f = 100MHz
Output Capacitance	C _{obo}	_	50		pF	V _{CB} = -10V, f = 1MHz
Input Capacitance	Cibo	_	300	_	pF	$V_{EB} = -5V$, $f = 1MHz$
SWITCHING CHARACTERISTICS						
Turn-On Time	ton	_	350	_	ns	V 20V I 750m A
Delay Time	t_d	_	180	_	ns	$V_{CC} = -30V, I_C = -750mA,$ $I_{B1} = -15mA$
Rise Time	t _r	_	170		ns	IB1 = - ISIIIA
Turn-Off Time	t _{off}	_	400	_	ns	V 20V I 750m A
Storage Time	t _s	_	300		ns	$V_{CC} = -30V, I_{C} = -750mA,$
Fall Time	t _f	_	100	_	ns	$I_{B1} = -I_{B2} = -15\text{mA}$

Note:

9. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%

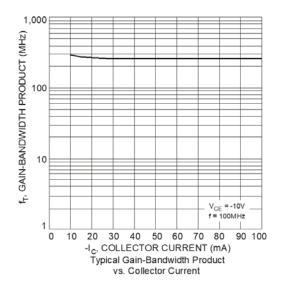


Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)





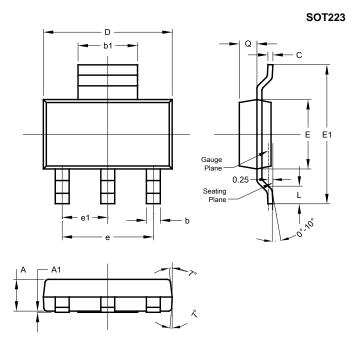
Typical Electrical Characteristics (continued)





Package Outline Dimensions

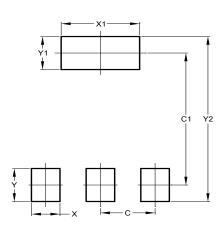
Please see http://www.diodes.com/package-outlines.html for the latest version.



SOT223					
Dim	Min	Max	Тур		
Α	1.55	1.65	1.60		
A1	0.010	0.15	0.05		
b	0.60	0.80	0.70		
b1	2.90	3.10	3.00		
С	0.20	0.30	0.25		
D	6.45	6.55	6.50		
Е	3.45	3.55	3.50		
E1	6.90	7.10	7.00		
е	_	_	4.60		
e1		_	2.30		
L	0.85	1.05	0.95		
Q	0.84	0.94	0.89		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



SOT223

Dimensions	Value (in mm)
С	2.30
C1	6.40
Х	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00



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